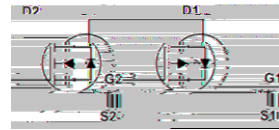


**Product Summary**

The ZMC88403D combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . It combines one N channel MOSFET and one P channel MOSFET.



Trench technology

$R_{DS(ON)}$  to minimize conductive loss

fast switching

Dual DIE in one package



Power Management in Notebook Computer

BLDC Motor driver

Part NO.	ZMC88403D
Marking	ZMC88403
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	2.3	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

**N Channel Absolute Maximum Ratings  $T_C = 25$** 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	20	V
Continuous Drain Current	$I_D @ T_C = 25$	30	A
	$I_D @ T_C = 75$	22.8	A
	$I_D @ T_C = 100$	19	A





**N Channel characteristics curve**

Fig.1 Power Dissipation Derating Curve

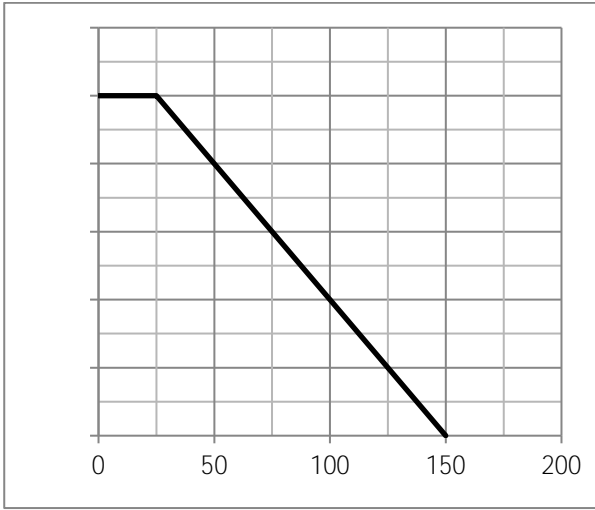


Fig.2 Typical output Characteristics

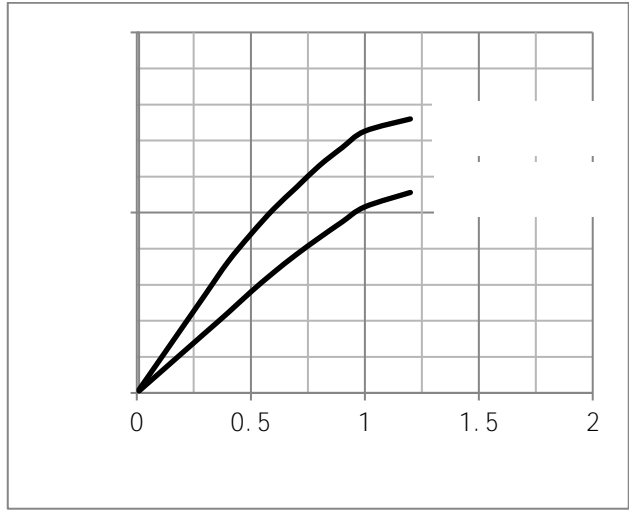


Fig.3 Threshold Voltage V.S Junction Temperature

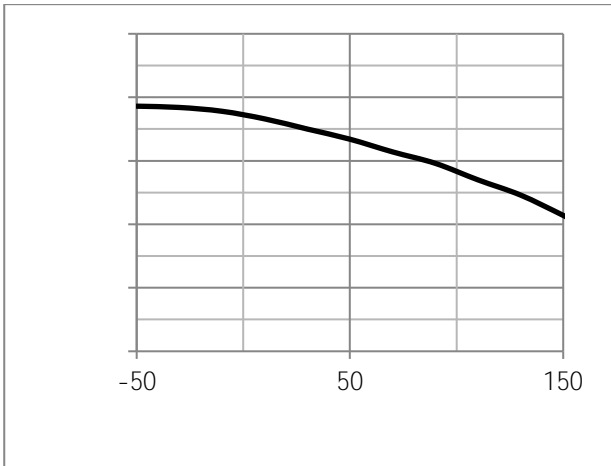
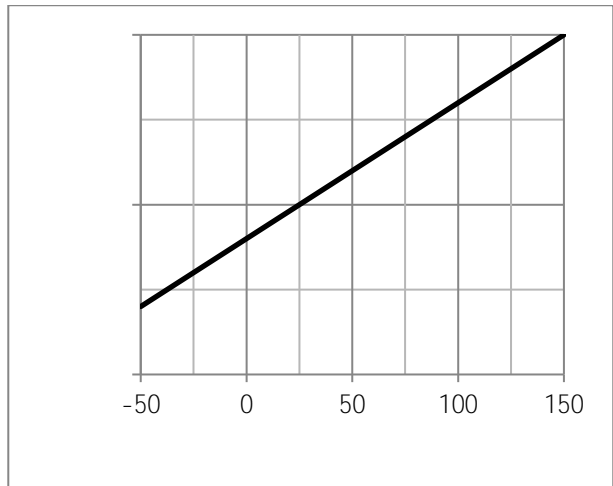
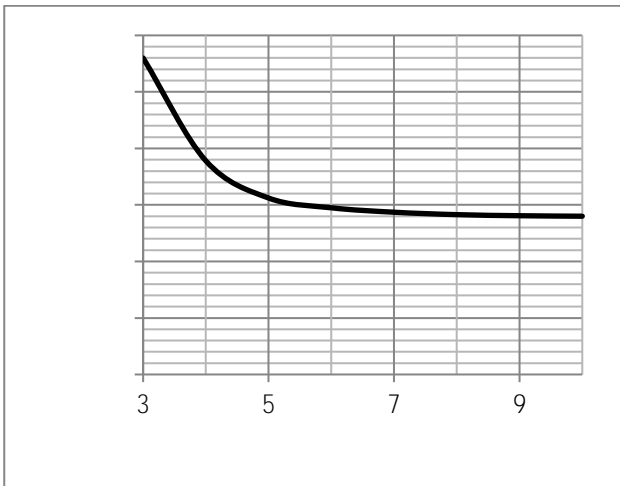
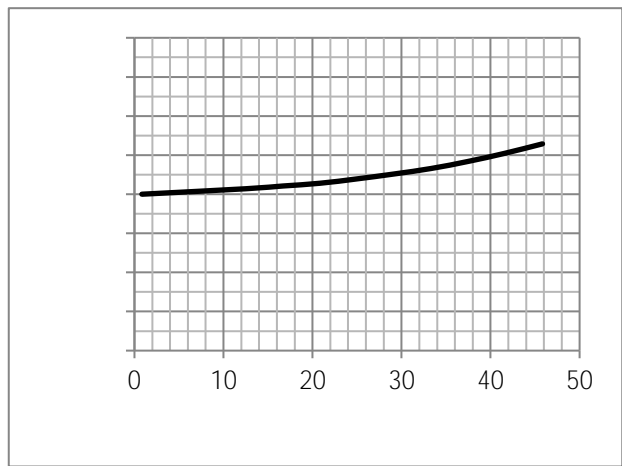


Fig.4 Resistance V.S Drain Current







**Test Circuit**

Fig.1 Switching Time Measurement Circuit

Fig.2 Gate Charge Waveform

Fig.3 Switching Time Measurement Circuit

Fig.4 Gate Charge Waveform

Fig.5 Avalanche Measurement Circuit

Fig.6 Avalanche Waveform



(TO-252-4)

Unit: mm

